

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization  
International Bureau



(43) International Publication Date  
12 July 2001 (12.07.2001)

PCT

(10) International Publication Number  
**WO 01/50516 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 21/336, 29/786**

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(21) International Application Number: PCT/GB01/00009

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU,

(22) International Filing Date: 2 January 2001 (02.01.2001)

AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CR, CU, CZ,

(25) Filing Language: English

DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR,

(26) Publication Language: English

HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR,

(30) Priority Data:  
0000374.9 7 January 2000 (07.01.2000) GB

LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ,

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NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM,

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TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW.

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(84) Designated States (*regional*): ARIPO patent (GH, GM,

KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian

patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European

patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE,

IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF,

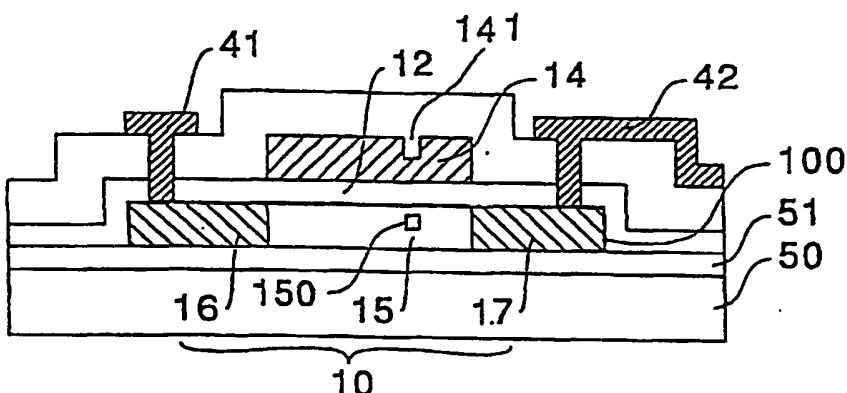
CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published:

— With international search report.

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD OF MANUFACTURING A THIN-FILM TRANSISTOR



(57) Abstract: In a TFT 10, a channel region (15) facing a gate electrode 14 through a gate insulating film (12), a source electrode (16) connected to the channel region (15) and a drain region (17) connected to the channel region (15) on the side opposite this source region (16) are formed in a polycrystal semiconductor film (100) that was patterned in island forms. In the channel region (15), a recombination center (150) is formed for capturing a small number of carriers (holes) by introducing impurities such as inert gases, metals, Group III elements, Group IV elements and Group V elements after a crystallization process is carried out on a semiconductor film (100). The invention thus provides an arrangement restraining bipolar transistor type behavior, to stabilize saturation current and to provide a TFT that can improve reliability.

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